

**Amendments to the Claims**

Claims 1-61 (Cancelled).

62. (Currently amended) A method of forming a semiconductor construction, comprising:

forming a layer of dielectric material over a semiconductive substrate material;

patterning the dielectric material utilizing photolithographic processing to form at least two patterned blocks, a pair of adjacent blocks being separated by a first gap, each block having a sidewall within the first gap formed during the photolithographic processing;

forming a pair of spacers along the sidewalls and within the first gap, the spacers having lateral edges separated by a second gap, the second gap being narrower than the first gap;

while the spacers remain along the sidewalls, implanting at least one dopant into the semiconductive material within the second gap to form a doped region;

removing the spacers from along the sidewalls; and

depositing a material comprising at least one of a metal and a metal nitride within the gap.

63. (Currently amended) The method of claim 62 further comprising after removing the spacers and prior to the depositing, forming conformally depositing a layer of polysilicon over the semiconductive material within the gap and along the sidewalls.

64. (Previously presented) The method of claim 62 further comprising planarizing the material.

65. (Previously presented) The method of claim 62 wherein the material comprises tungsten.

66. (Previously presented) The method of claim 62 wherein the at least one dopant comprises indium.

67. (Previously presented) The method of claim 62 wherein the second gap is less than or equal to half the width of the first gap.